

HAT2036R

Silicon N Channel Power MOS FET
Power Switching

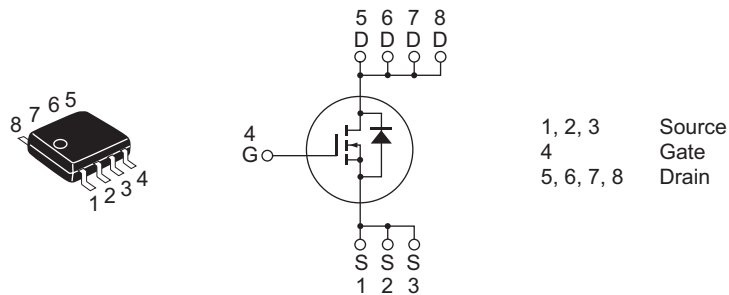
REJ03G1166-0600
(Previous: ADE-208-665D)
Rev.6.00
Sep 07, 2005

Features

- Low on-resistance
 $R_{DS(on)} = 12\text{ m}\Omega$ typ
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- High speed switching
 $t_f = 60\text{ ns}$ typ.

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8 <FP-8DAV>)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	12	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	96	A
Body-drain diode reverse drain current	I_{DR}	12	A
Channel dissipation	P_{ch} ^{Note 2}	2.5	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$ 2. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), $PW \leq 10 s$

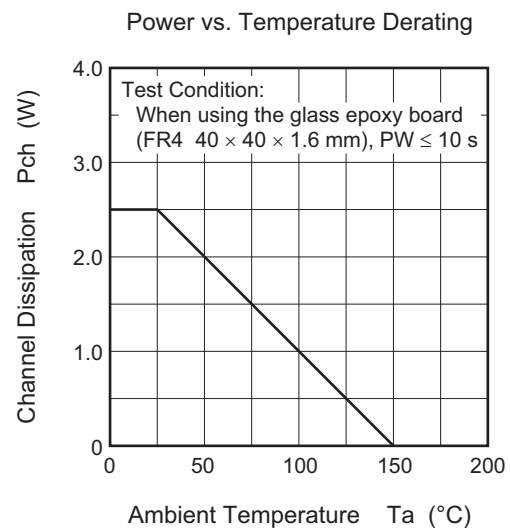
Electrical Characteristics

(Ta = 25°C)

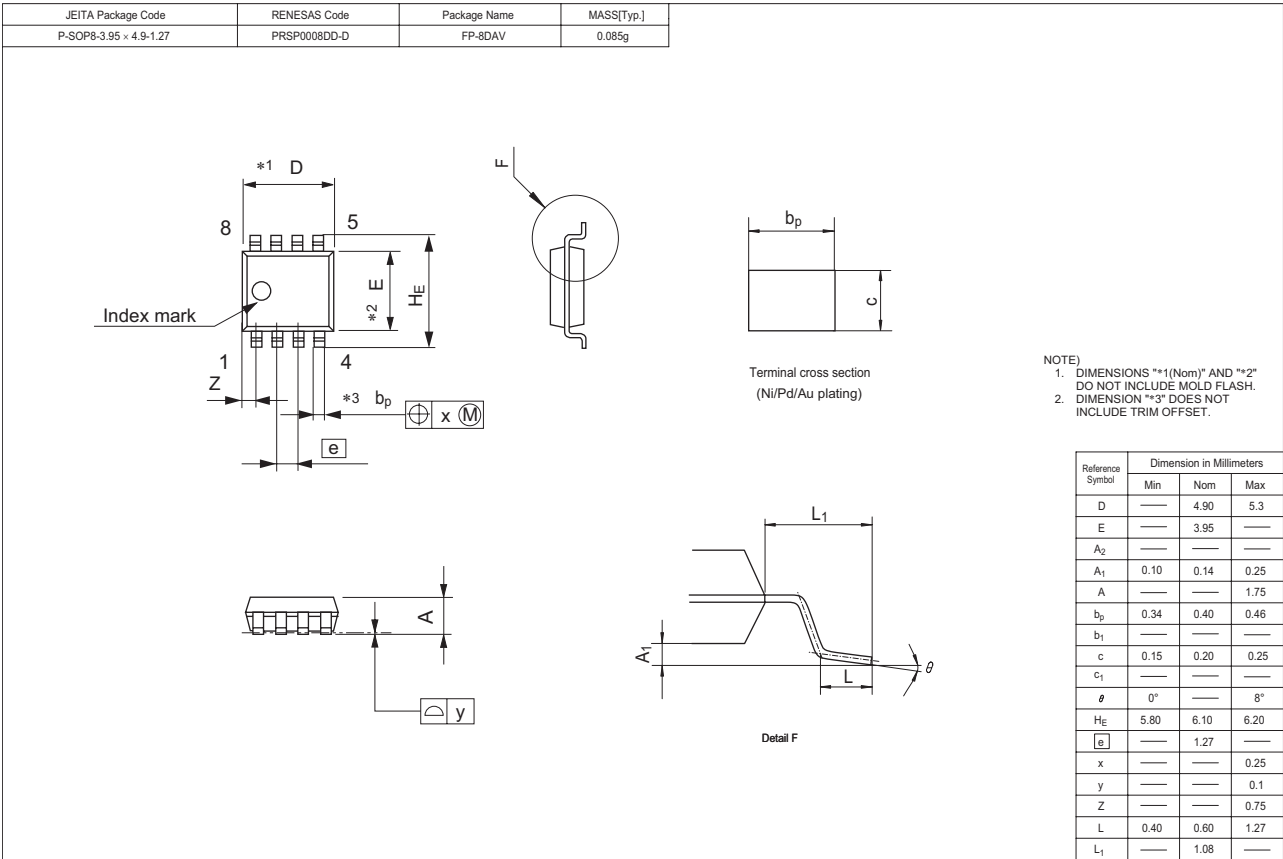
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	3.0	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	12	15	mΩ	$I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note 3}
	$R_{DS(on)}$	—	20	30	mΩ	$I_D = 6 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	12	20	—	S	$I_D = 6 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note 3}
Input capacitance	C_{iss}	—	1200	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	380	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	200	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	23	—	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	4.0	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	6.0	—	nC	$I_D = 12 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	40	—	ns	$V_{GS} = 4.5 \text{ V}$, $I_D = 6 \text{ A}$, $V_{DD} \cong 10 \text{ V}$
Rise time	t_r	—	300	—	ns	
Turn-off delay time	$t_{d(off)}$	—	35	—	ns	
Fall time	t_f	—	60	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 12 \text{ A}$, $V_{GS} = 0$ ^{Note 3}
Body-drain diode reverse recovery time	t_{rr}	—	35	—	ns	$I_F = 12 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 20 \text{ A}/\mu s$

Note: 3. Pulse test

Main Characteristics



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2036R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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